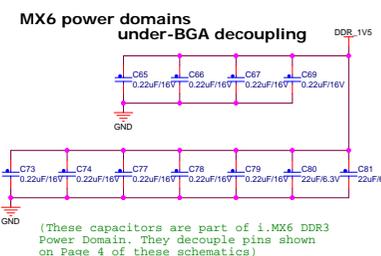
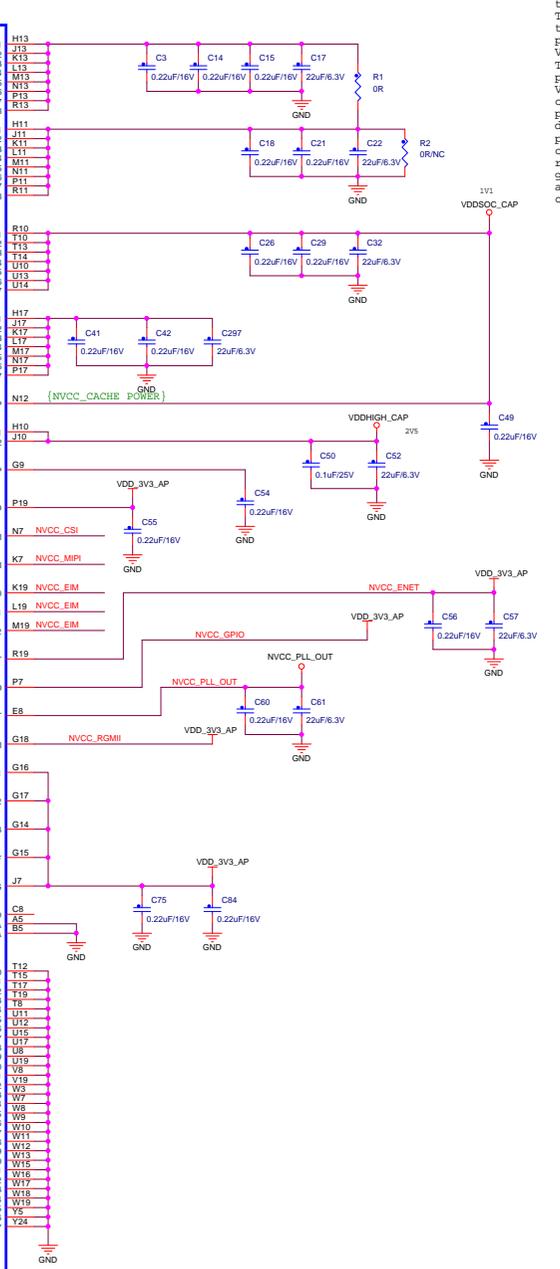
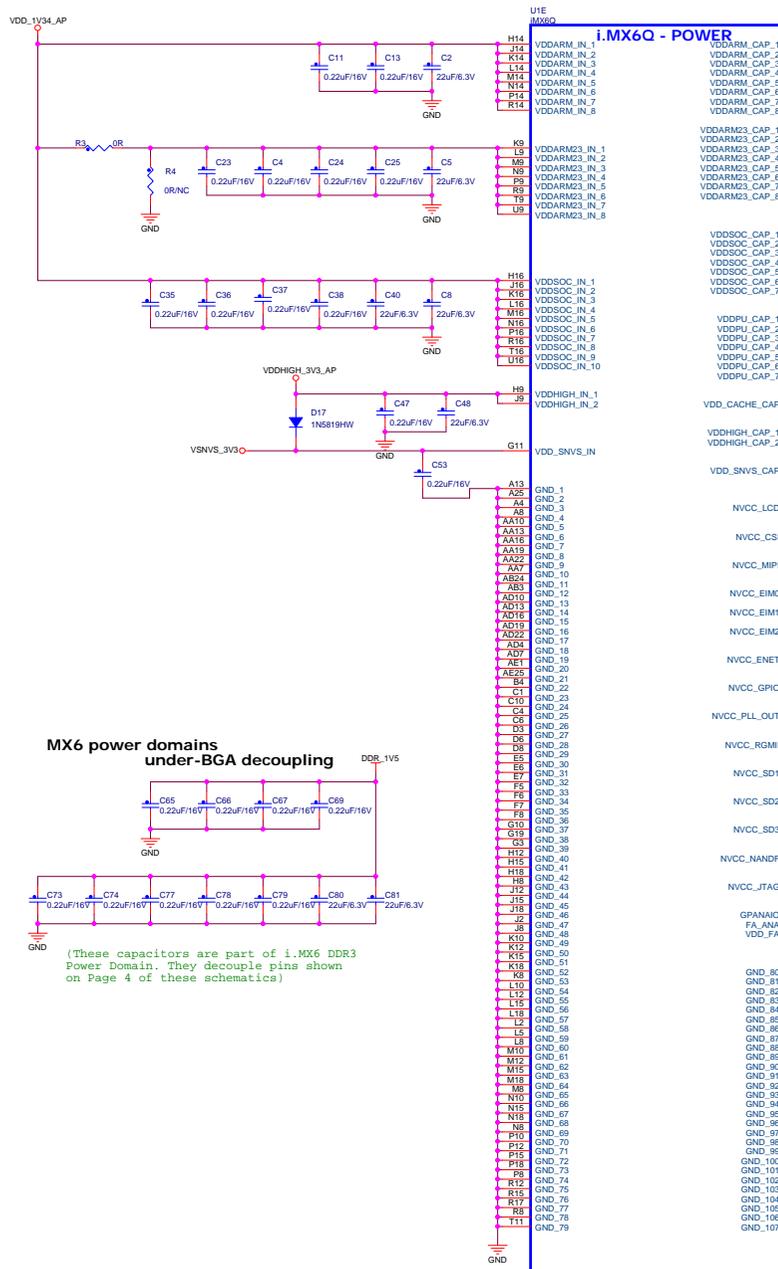


Revision History

V1.0 Initial Released

| | | | |
|---|-----------------|---|---------------|
|  天嵌科技 EMBEDSKY TECH | | http://www.embedsky.com | |
| Title | | | |
| E9 | | | |
| Size | Document Number | | Rev |
| A | <Doc> | | 3 |
| Date: | | Thursday, August 18, 2016 | Sheet 1 of 15 |

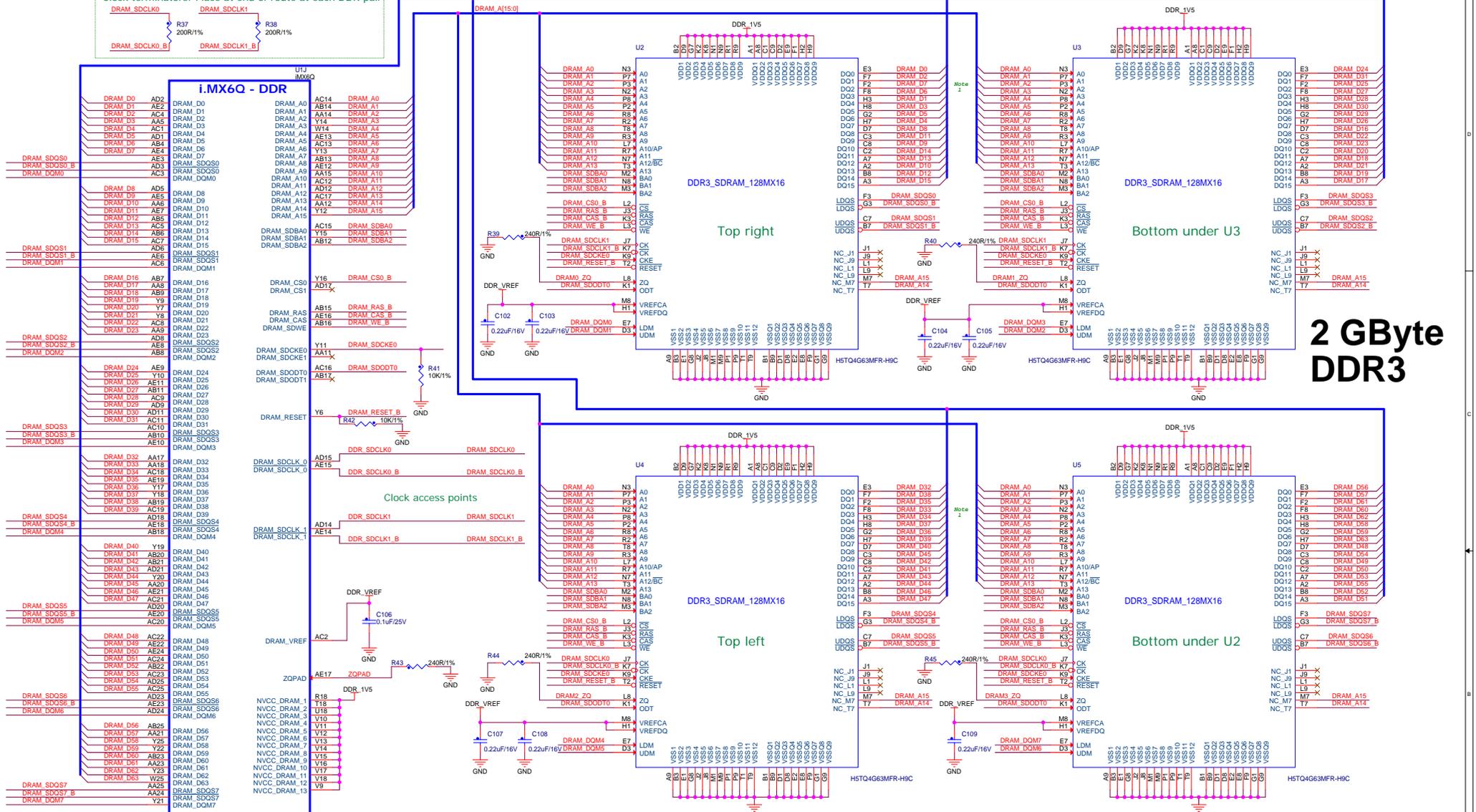


NOTE:
 The VDDARM_CAP and VDDARM23_CAP rails have been optimized for use with the i.MX 6 Quad and i.MX 6 DualLite processors.
 To achieve the lowest power mode (preventing internal leakage) when using the i.MX 6 Dual and the i.MX 6 SoloLite processors, VDDARM_CAP should be split from VDDARM23_CAP and the VDDARM23_CAP pins should be connected to ground.
 This can be done on a single board configured for use with all four processors by placing a single 0 Ohm resistor between the VDDARM_CAP and VDDARM23_CAP rails (in place of the straight net connection). To use the board with different processors, populate the resistor when using Quad and DualLite processors and depopulate resistor when using Dual and SoloLite processors. When using Dual and SoloLite processors, depopulate the capacitors attached to VDDARM23_CAP pins and replace one of the capacitors with a zero Ohm resistor to short pins to ground. The configuration in this schematic will work with all four processors, but will not result in the most power optimized configuration for the i.MX 6 Dual and Solo processors.

LAYOUT NOTE:
 It is critical that the bulk and decoupling capacitors placed on the VDDARM_CAP, VDDARM23_CAP, VDDSOC_CAP and VDDPU rails be placed directly underneath the processors. Development testing has shown that proper placement of the capacitors can reduce ripple on the voltage rails by as much as 50% compared to placing capacitors outside the physical boundaries of the processor. These will result in more stable processor operations.

Clock terminators: Place at end of route at each DDR pair

DRAM_SDCLK0
R37 200R/1%
DRAM_SDCLK1
R38 200R/1%



**2 GByte
DDR3**

NOTE 1:

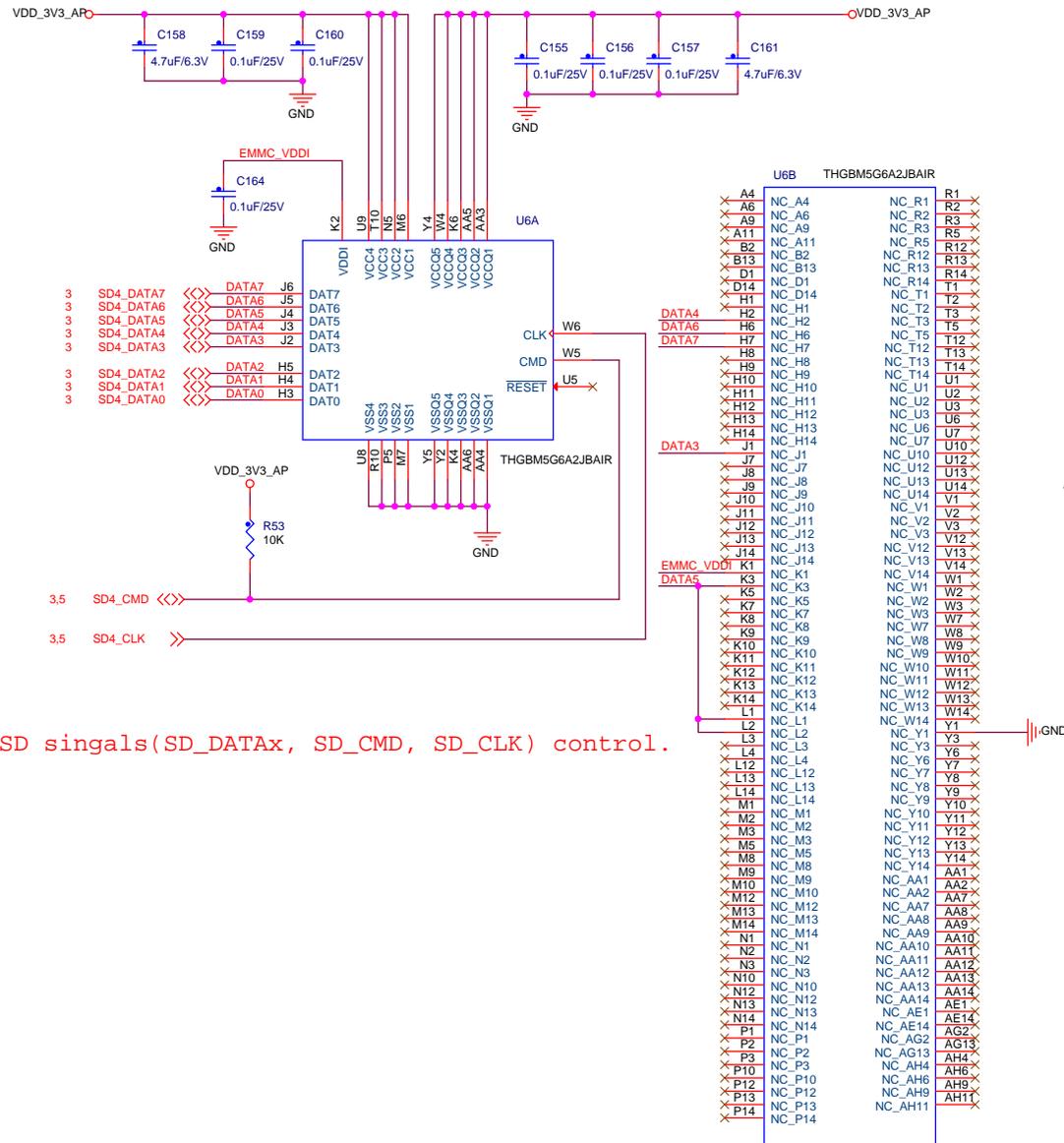
Using bit swapping for DATA bus to allow easy pcb routing.

When using data bit swapping the low order bit of each byte must reside at bit 0 of the byte. The remaining 7 data bits can be swapped freely. This restriction is for write leveling calibration.

Example D0 to D0 or D0 to D8, and D1-7 can be swapped.

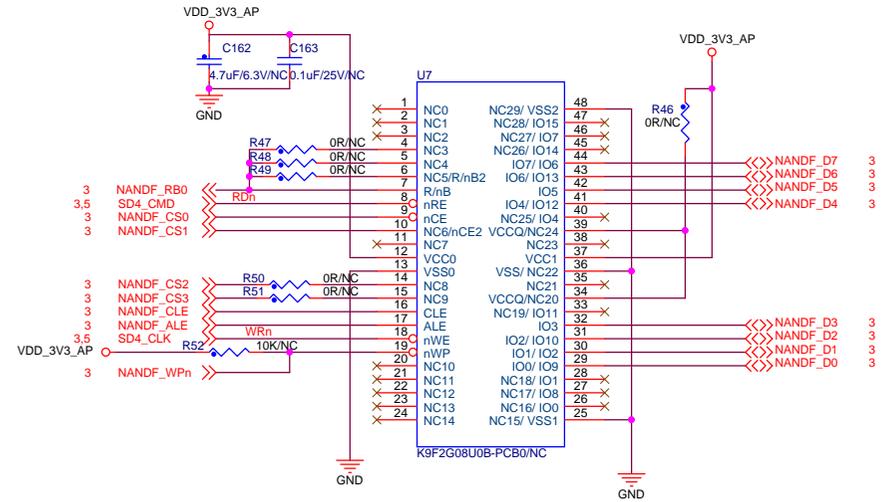
When swapping byte lanes on 16-bit memories, remember to move the DQmX, DQsX, and DQsX_B signals for that byte lane.

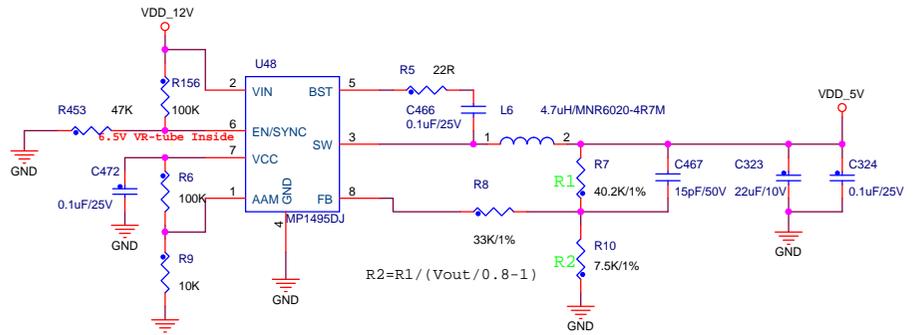
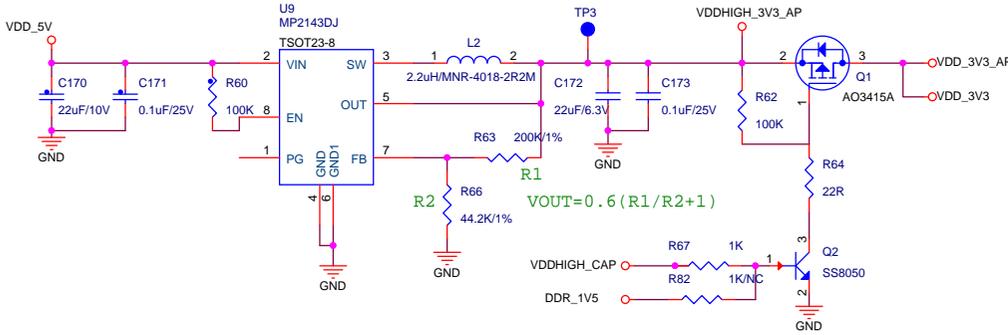
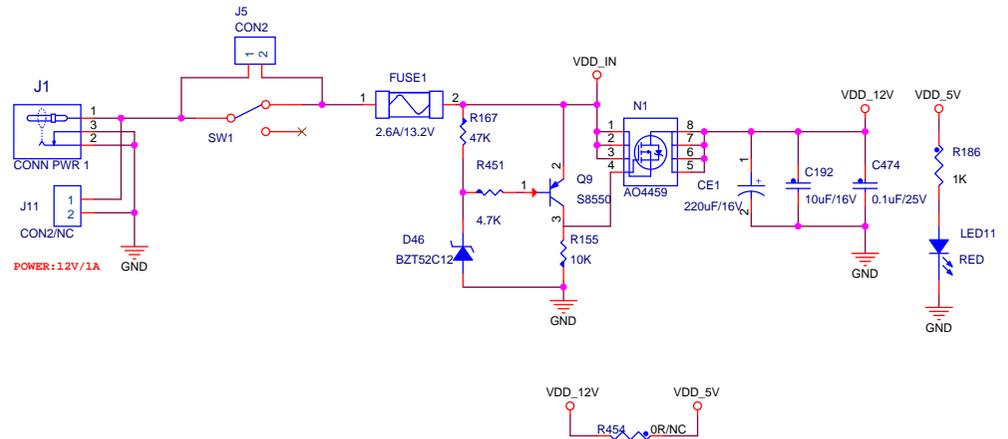
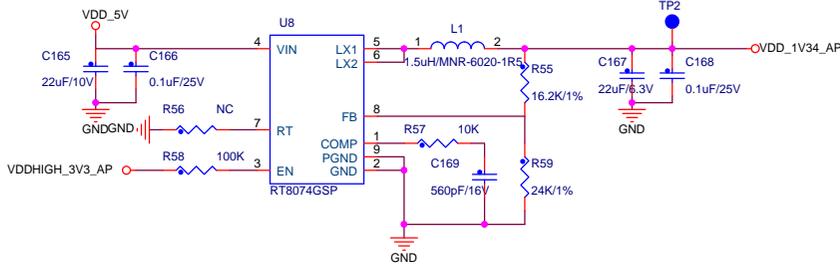
8GB eMMC MEMORY



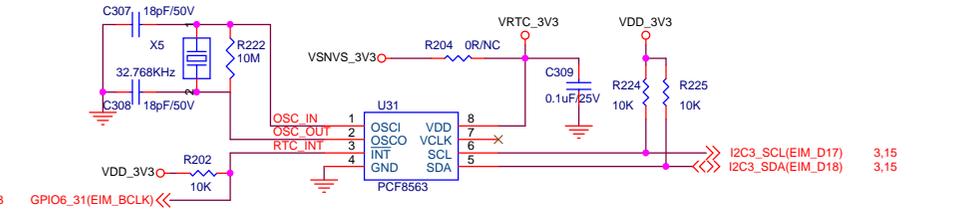
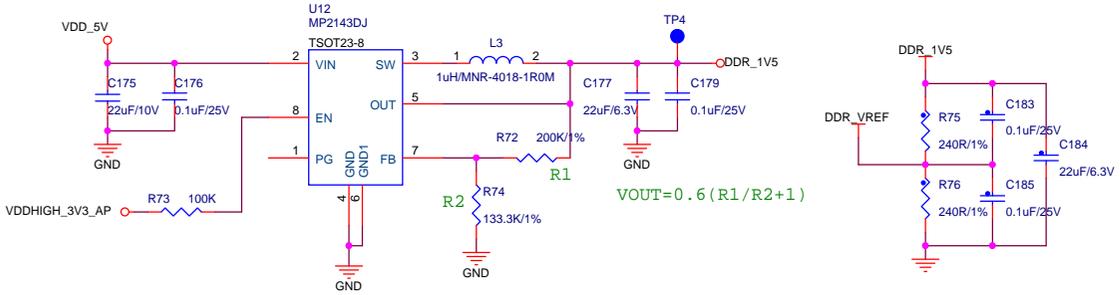
Layout:
50ohm, SD singals(SD_DATAx, SD_CMD, SD_CLK) control.

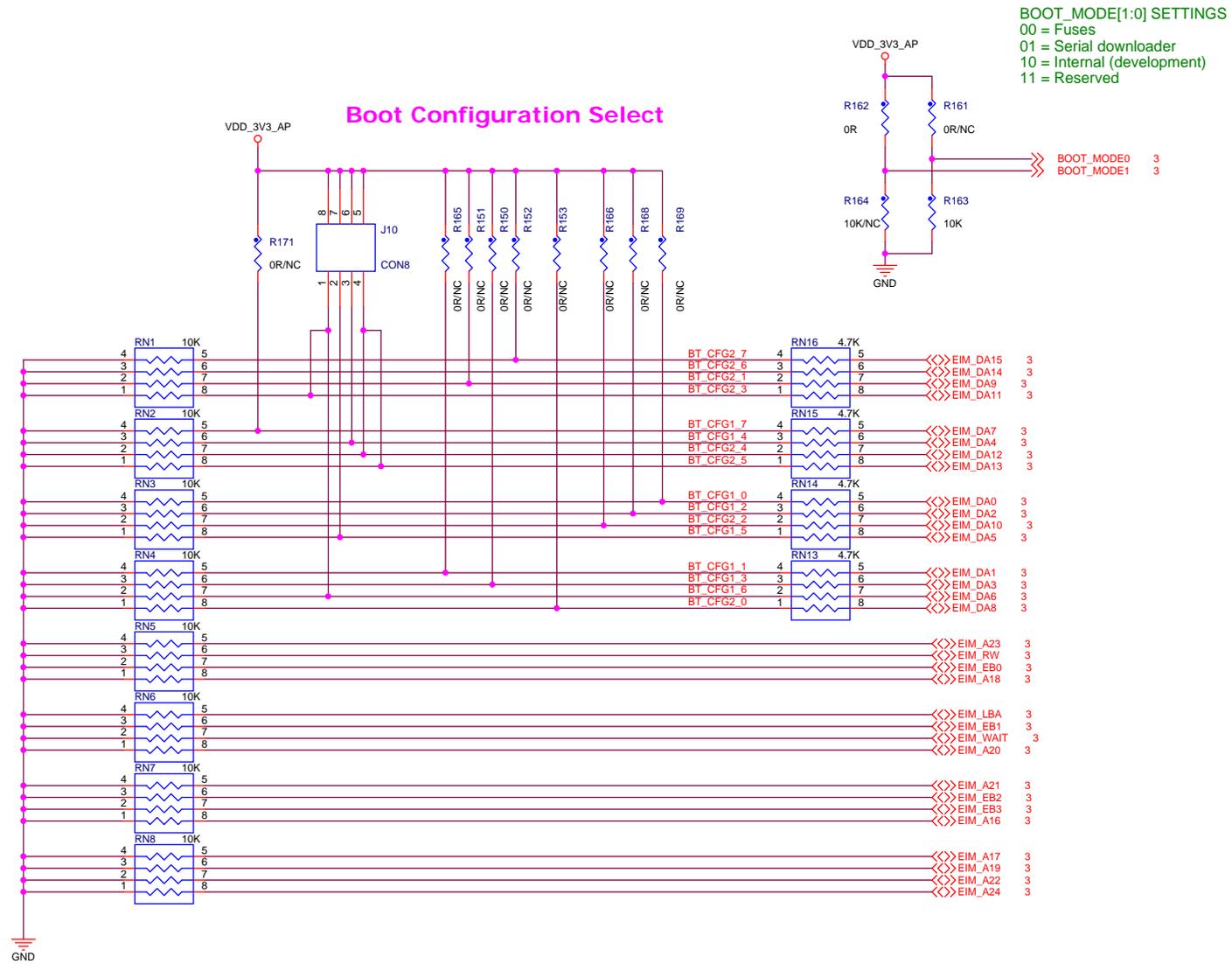
NAND Flash memory





12V to 5V Switching Regulator with 2A output current

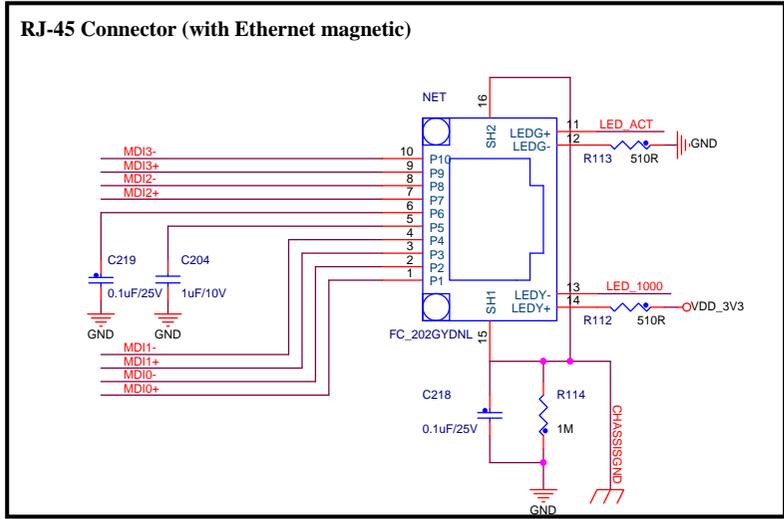
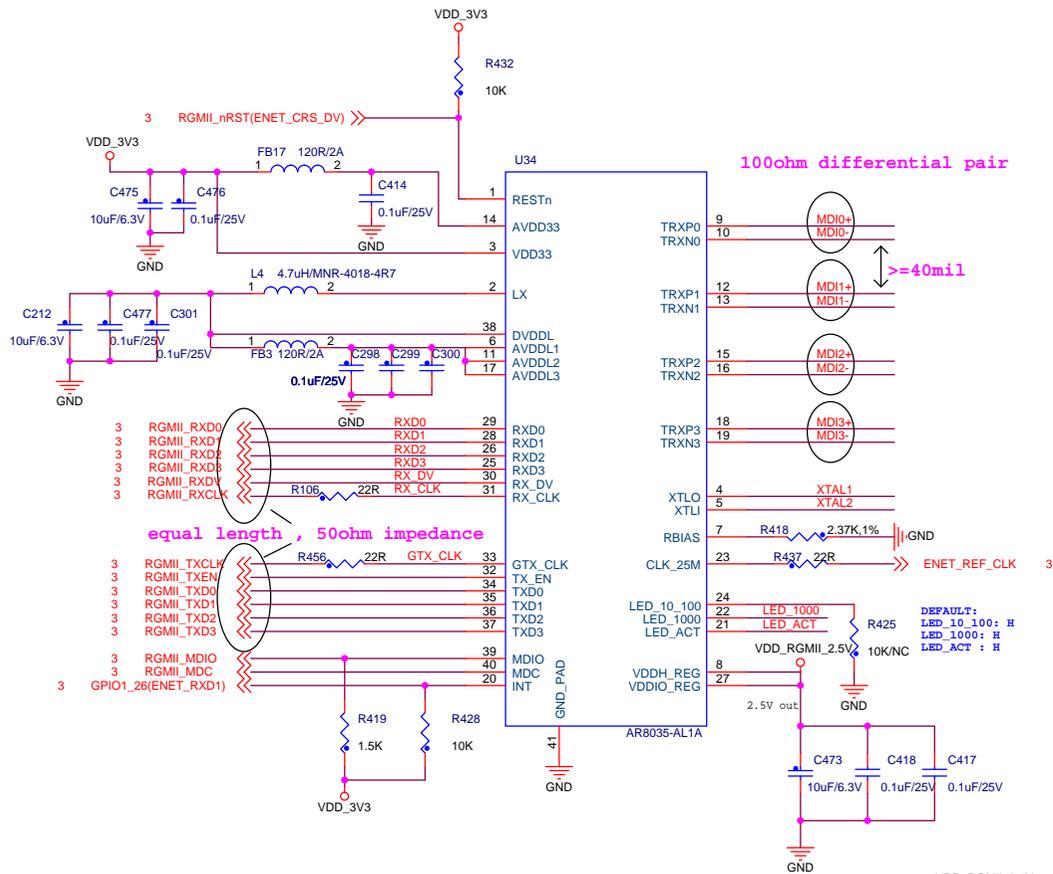




Boot Configuration Select

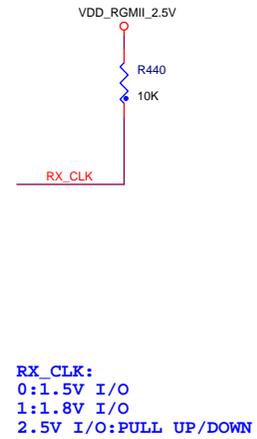
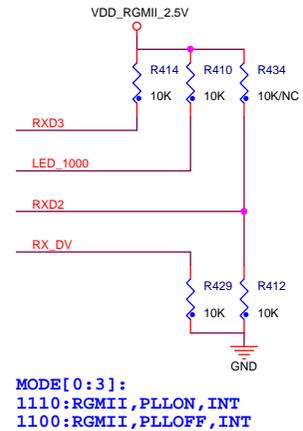
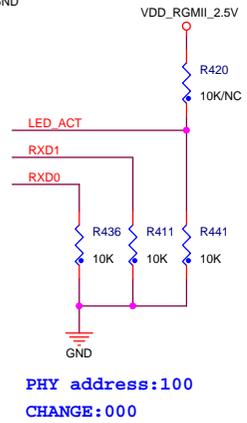
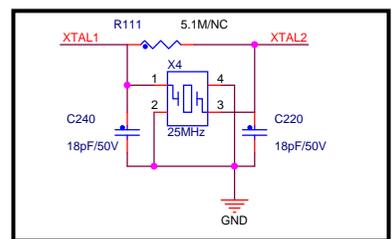
| G1-6 G2-3 | G1-5 | G1-4 | G2-5 G2-4 | MODE |
|--------------|------|------|--------------|-----------|
| 1 | 0 | 0 | 0 | SD2_Boot |
| 1 | 1 | 0 | 1 | eMMC_Boot |
| 0 | 1 | 1 | 0 | DownLoad |

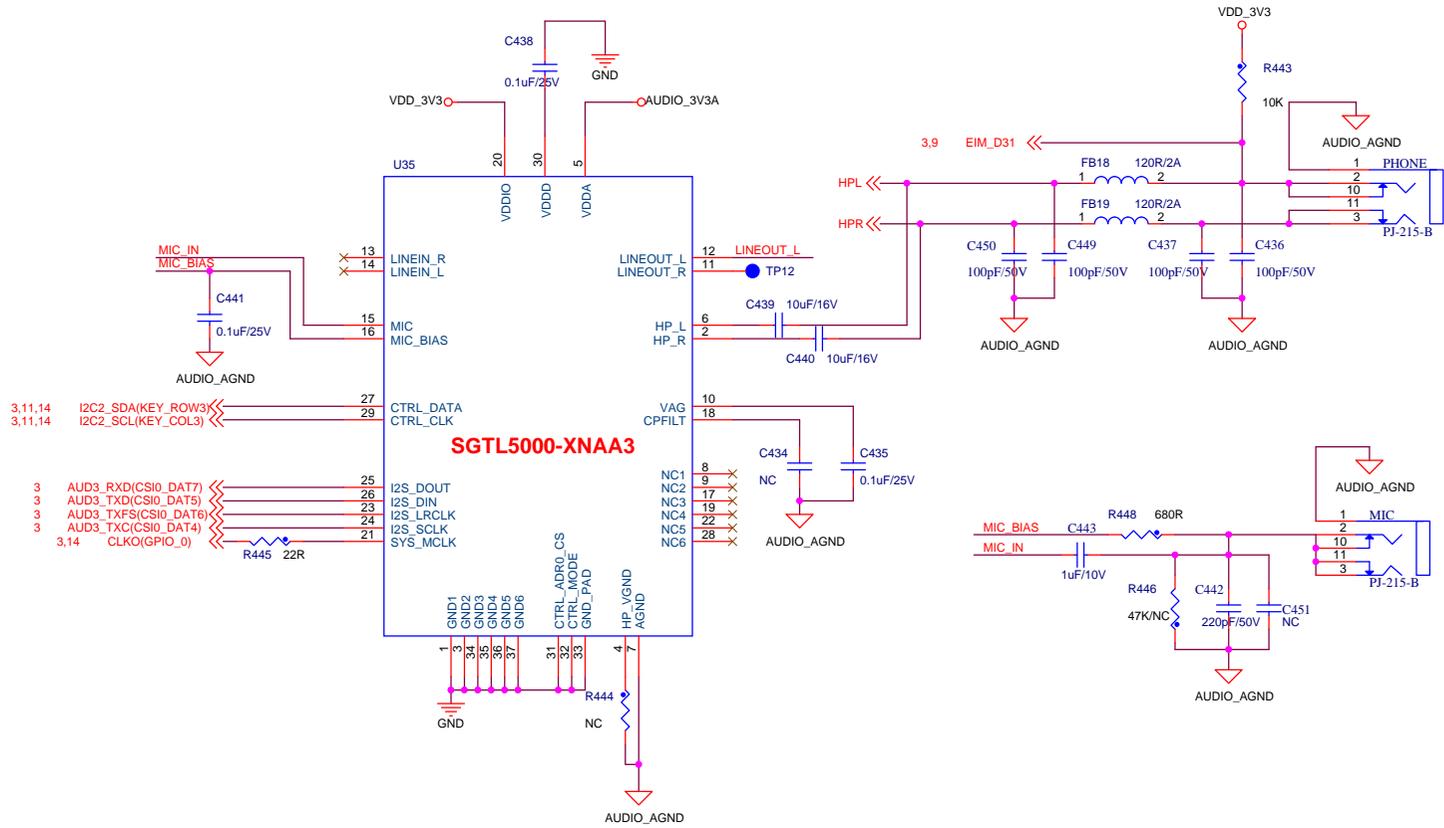
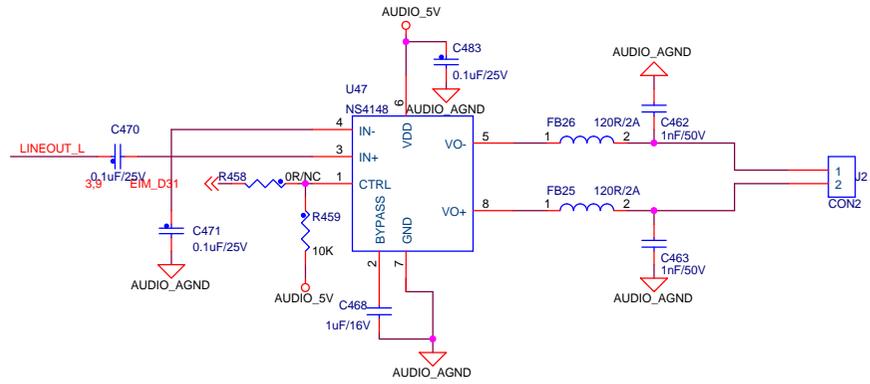
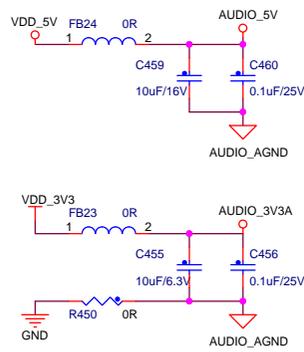
BT_CFG2_3 BT_CFG1_5 BT_CFG1_4 BT_CFG2_4
 BT_CFG1_6 BT_CFG2_5

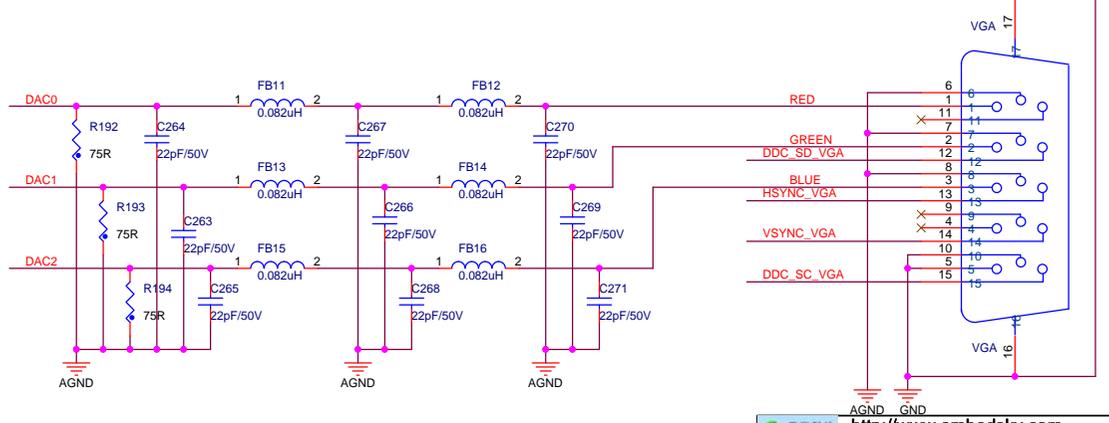
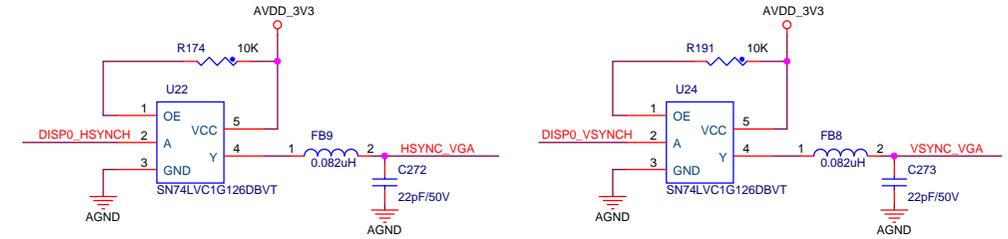
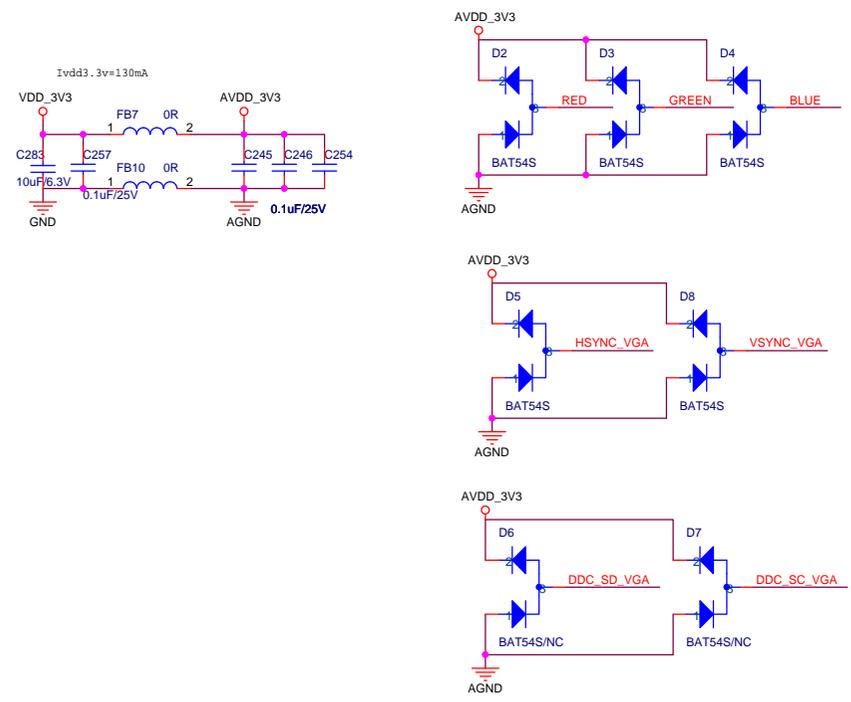
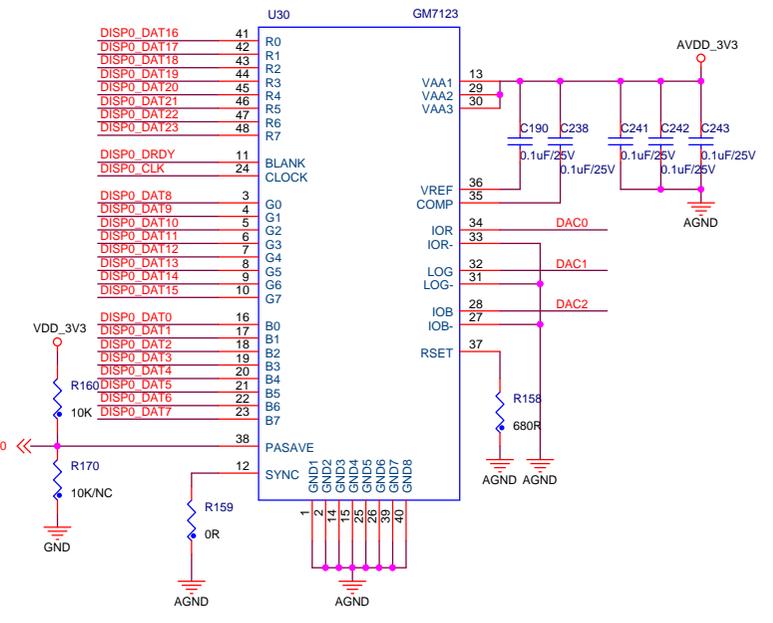
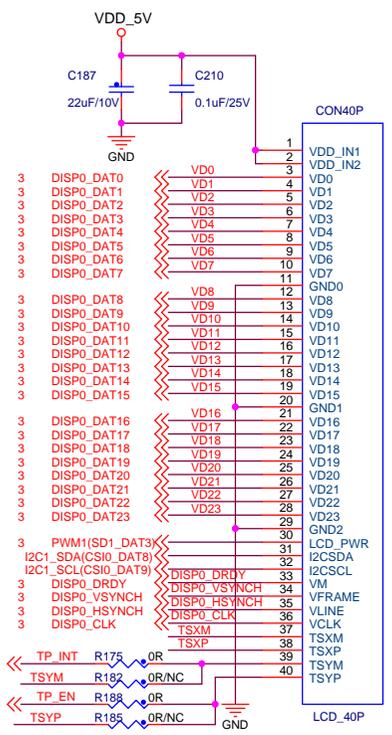
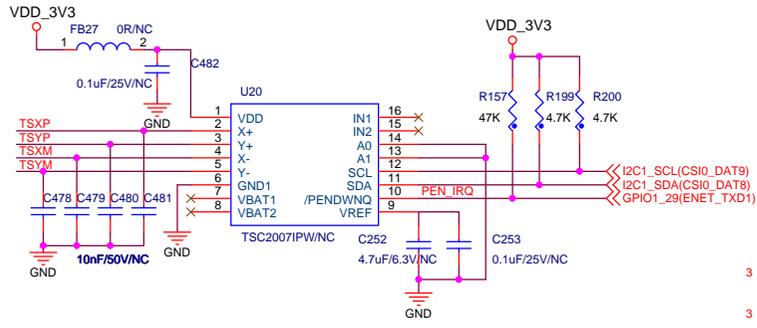
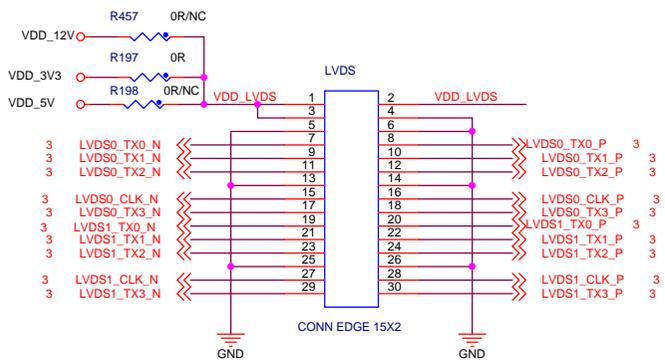


***Note:**
 L5 (4.7uH) should be as close to AR8035-AL1A LX pin (within 200mils).
 The CT14 and C424 capacitors as close to L5 if possible.

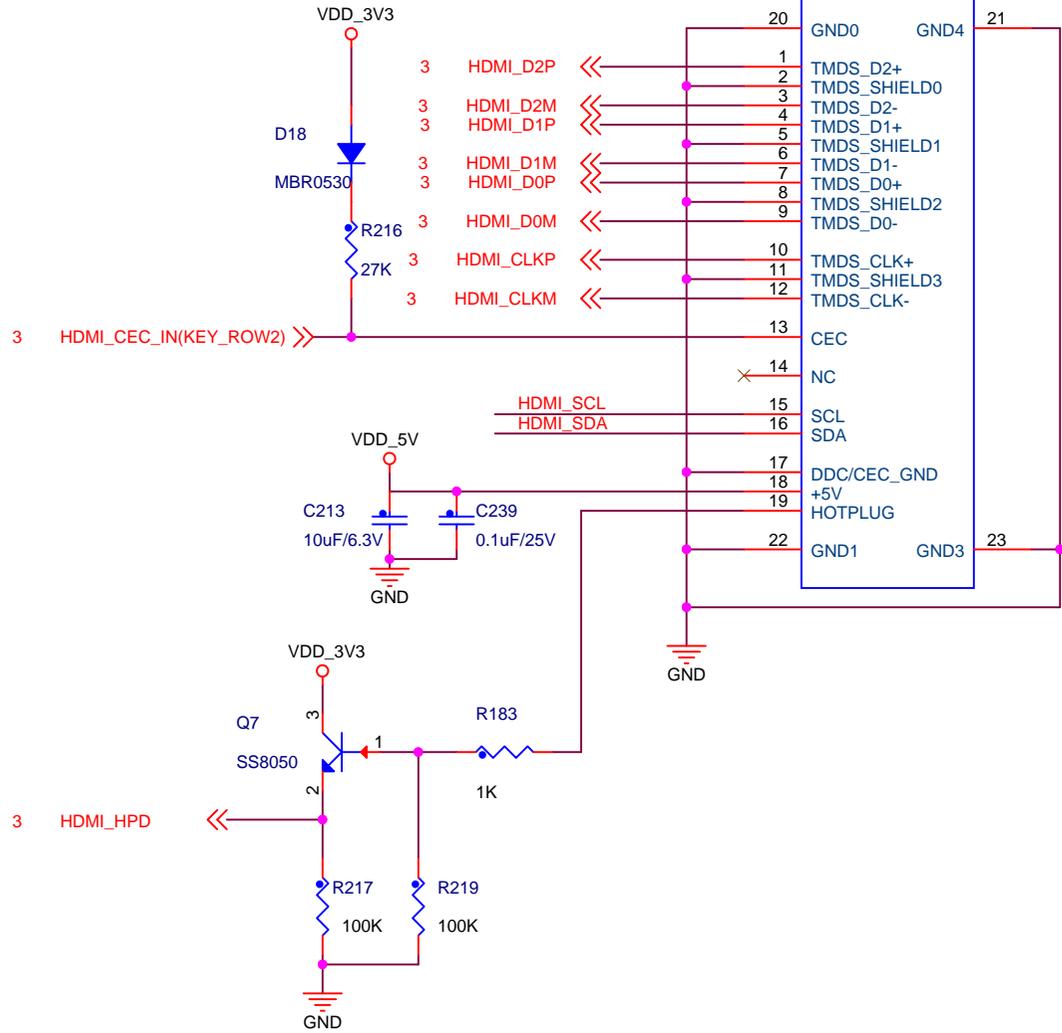
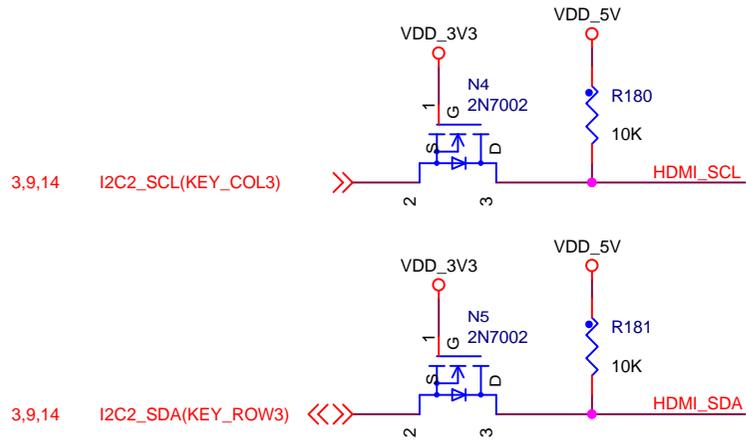
25MHz +- 50ppm Crystal

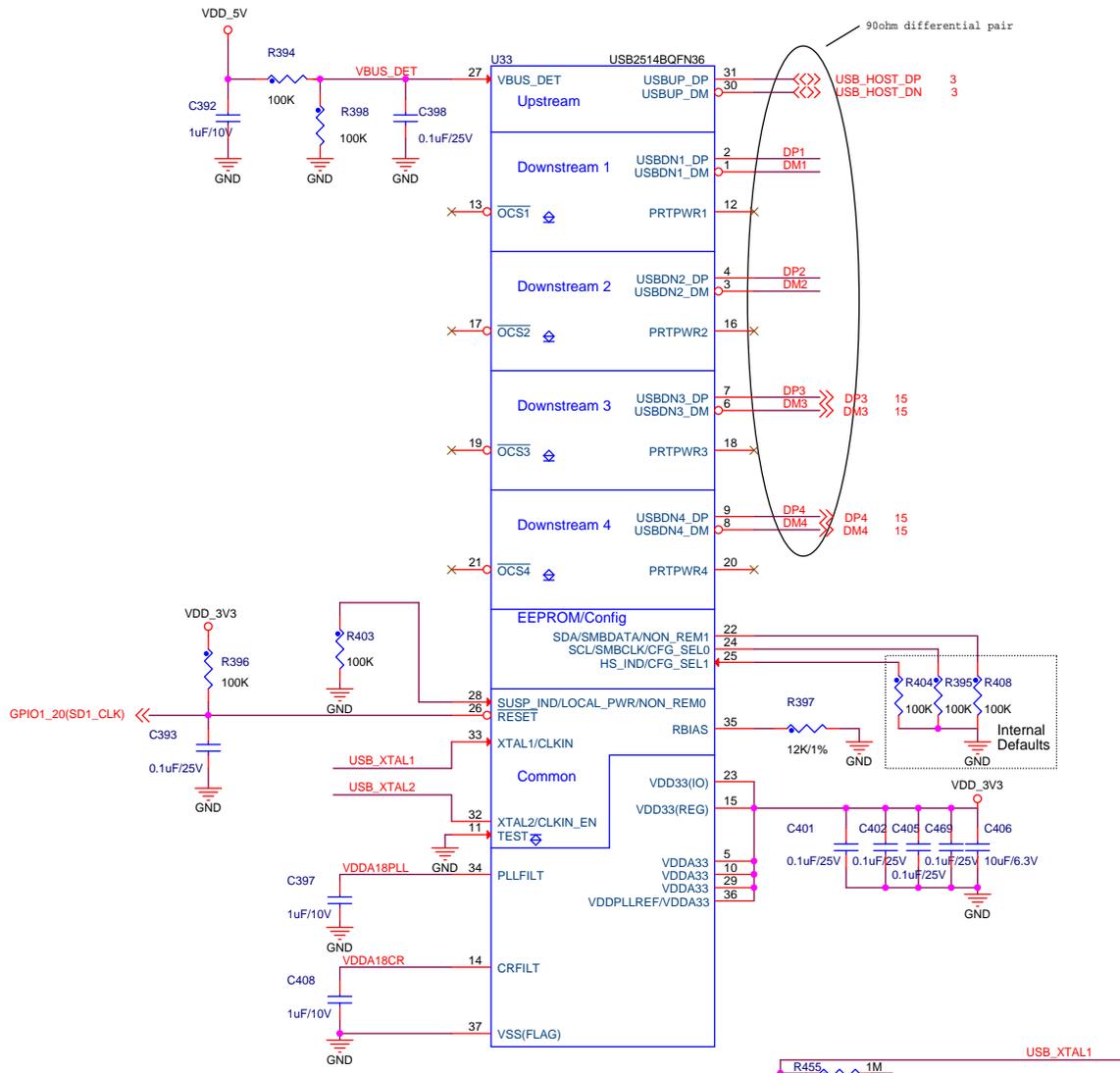




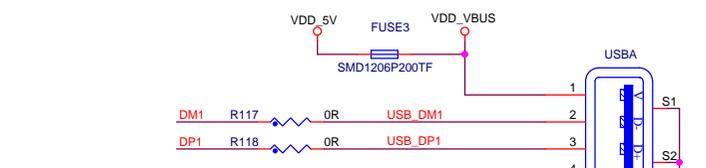
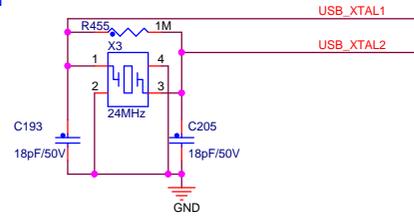


HDMI

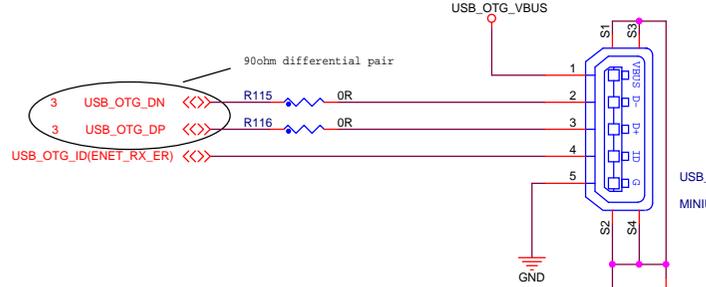
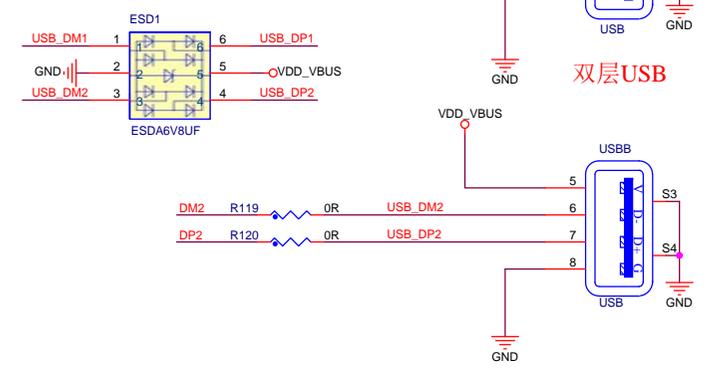




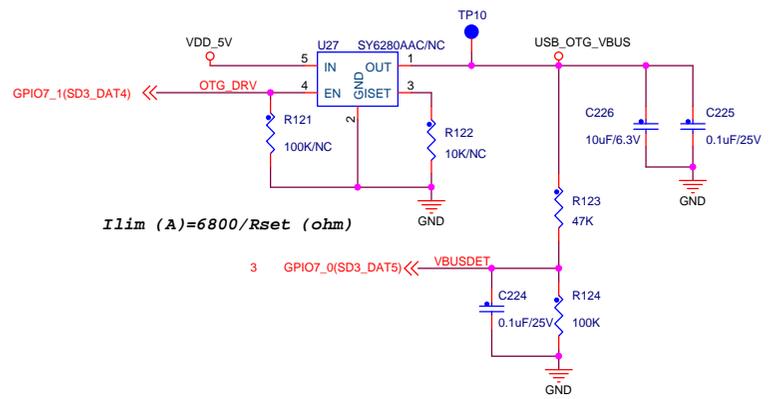
FRTPWR[4:1] Status
 1 : Battery charging feature is supported for port x
 0 : Battery charging feature is not supported for port x



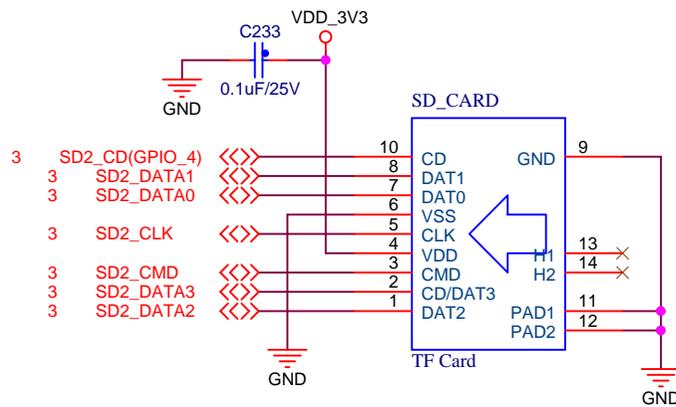
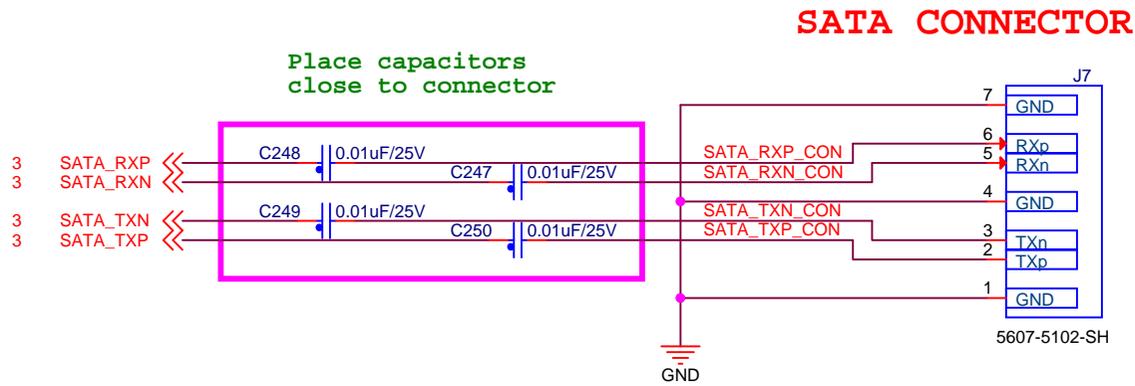
双层USB



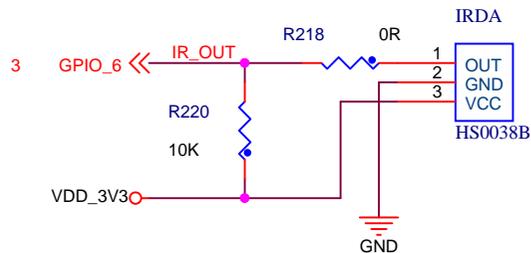
USB_OTG电路



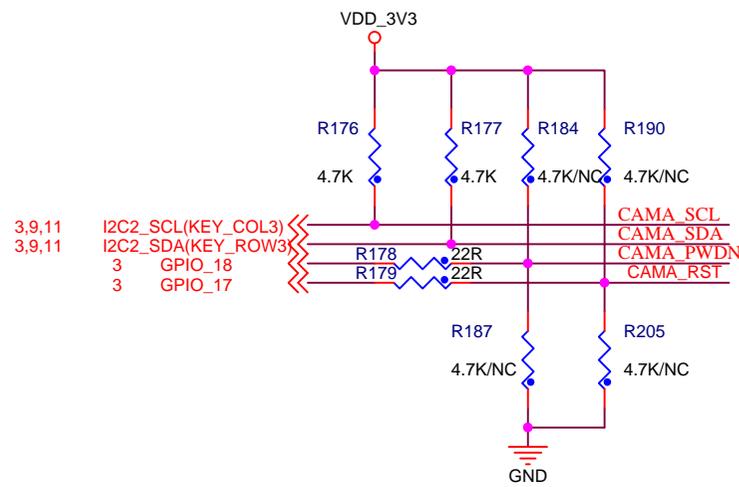
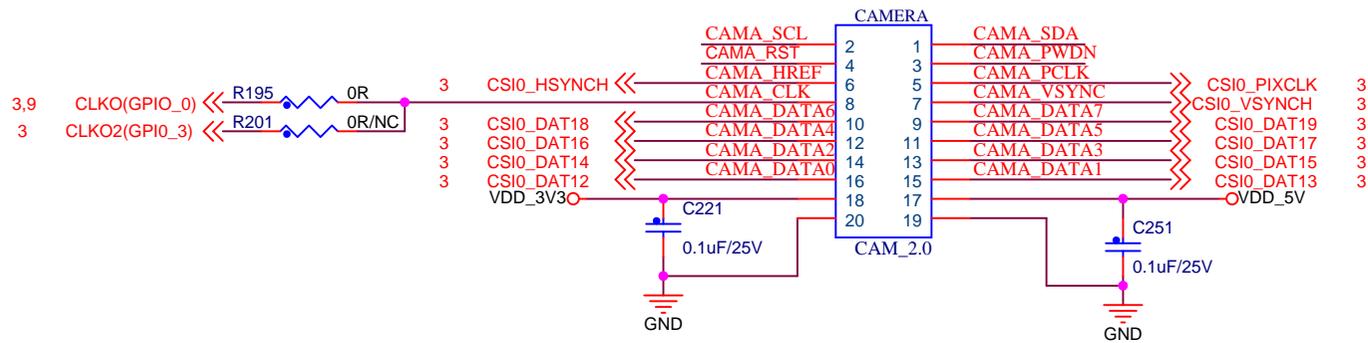
$$I_{lim} (A) = 6800 / R_{set} (ohm)$$

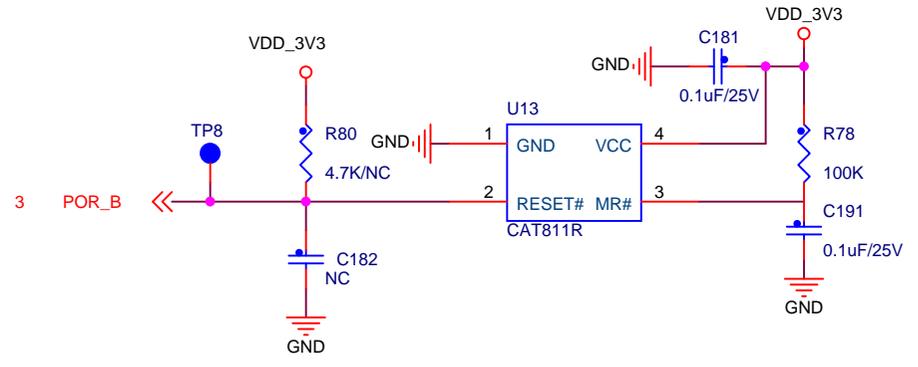
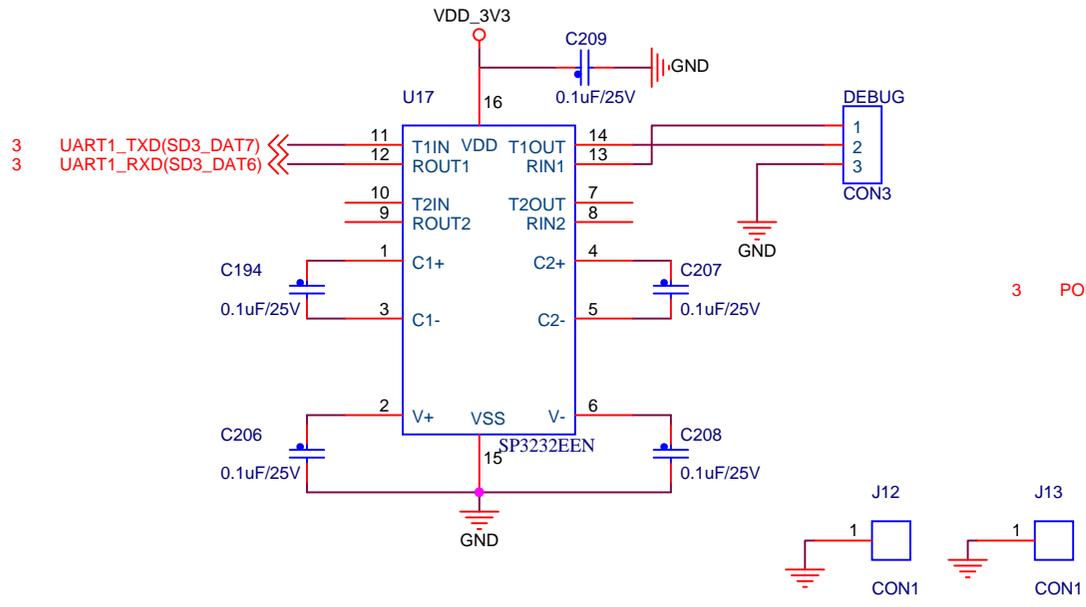


红外电路

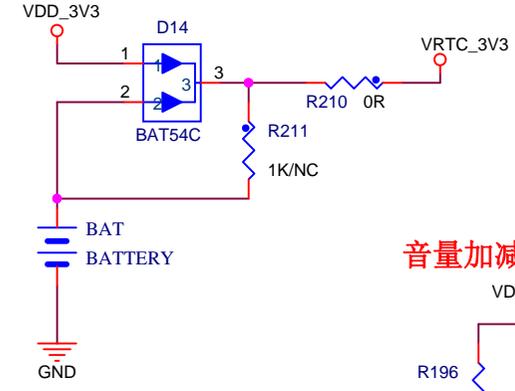


CAMMER A

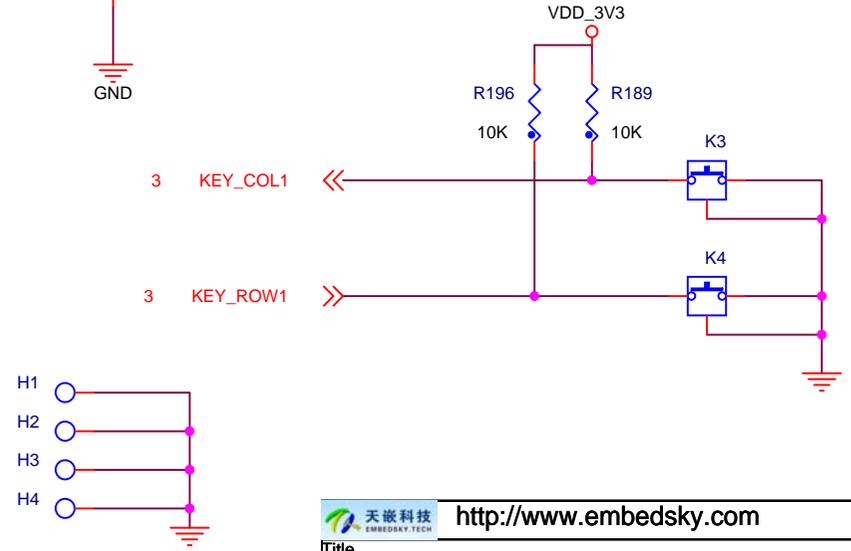




RTC电路



音量加减控制按键



扩展接口

